

Please Direct All Correspondence to Customer Number **20995**

TRANSMITTAL LETTER
INFORMATION DISCLOSURE STATEMENT

Applicant : Camm, et al.
App. No : 10/777,995
Filed : February 12, 2004
For : HIGH-INTENSITY
ELECTROMAGNETIC RADIATION
APPARATUS AND METHODS
Examiner : Won, Bumsuk
Art Unit : 2879

CERTIFICATE OF MAILING

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first-class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

July 18, 2006

(Date)

Che S. Chereskin

Che Swyden Chereskin, Ph.D., Reg. No. 41,466

Mail Stop Amendment

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Dear Sir:

Enclosed for filing in the above-identified application are:

- (X) An Information Disclosure Statement and PTO/SB/08 equivalent listing 8 references for consideration. Five references are enclosed.
- (X) The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.
- (X) Return prepaid postcard.

Che S. Chereskin

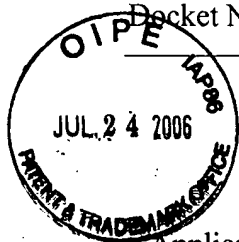
Che Swyden Chereskin, Ph.D.

Registration No. 41,466

Agent of Record

Customer No. 20,995

(949) 760-0404



INFORMATION DISCLOSURE STATEMENT

Applicant : Camm, et al.
App. No : 10/777,995
Filed : February 12, 2004
For : HIGH-INTENSITY
ELECTROMAGNETIC RADIATION
APPARATUS AND METHODS
Examiner : Won, Bumsuk
Art Unit : 2879

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed for filing in the above-identified application is a PTO/SB/08 Equivalent listing 8 references to be considered by the Examiner. Five references are provided.

This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required. If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: July 18, 2006

By: Che S. Chereskin

Che Swyden Chereskin, Ph.D.
Registration No. 41,466
Agent of Record
Customer No. 20,995
(949) 760-0404



INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Atty. Docket No. SMARB11.011AUS (82145-12)	Serial No. 10/777,995
	Applicant(s) CAMM, David Malcolm, et al.	
	Filing Date February 12, 2004	Group 2879

U.S. PATENT DOCUMENTS

* Examiner Initial		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A1	5,168,194	12-01-1992	Littlechild et al.	313	632	08-28-1991
	A2	6,608,967	08-19-2003	Arrison	392	407	06-07-2000
	A3	6,885,815	04-26-2005	Kusuda et al.	392	416	07-16-2003

FOREIGN PATENT DOCUMENTS

* Examiner Initial		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
	B1	CA 1,239,437	07-19-1988	CA	H01J 61	52		
	B2	GB 1468137	03-23-1977	UK				
	B3	WO 2005/078762 A3 (ISR)	06-01-2006	PCT	H01J 61	00		

OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

	C1	Gelpey, J. C., et al., "Advanced Annealing for Sub-130nm Junction Formation", 201st Electrochemical Society Meeting, Symposium Q1, Rapid Thermal and Other Short-Time Processing Technologies III, May 12-17, 2002, paper 735 (May 2002).
	C2	Tichy, R. S., et al., "Annealing of Ultra-Shallow Implanted Junctions Using Arc-Lamp Technology: Achieving the 90 nm Node", 9th IEEE International Conference on Advanced Thermal Processing of Semiconductors - RTP 2001 (Sept. 2001).

EXAMINER	DATE CONSIDERED
-----------------	------------------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-A820 (also form PTO-1449) P09C/REV03 Patent and Trademark Office * U.S. DEPARTMENT OF COMMERCE